

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Kie Y. Ahn et al.

Title: ATOMIC LAYER DEPOSITED  $\text{AlaAlO}_3$  FILMS FOR GATE DIELECTRICS

Docket No.: 1303.050US2

Filed: February 27, 2004

Examiner: Allan R. Wilson

Serial No.: 10/789,042

Due Date: N/A

Group Art Unit: 2815

**MS Amendment**

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

We are transmitting herewith the following attached items (as indicated with an "X"):

- ☒ Return postcard.
- ☒ Supplemental Information Disclosure Statement (2 pgs.), Form 1449 (4 pgs.), and copies of 7 cited documents.
- ☒ Authorization to charge Deposit Account 19-0743 in the amount of \$180.00 to cover the fee for consideration of Information Disclosure Statement under 97(c).

If not provided for in a separate paper filed herewith, Please consider this a PETITION FOR EXTENSION OF TIME for sufficient number of months to enter these papers and please charge any additional fees or credit overpayment to Deposit Account No. 19-0743.

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.

Customer Number 21186

By: David R. Cochran

Atty: David R. Cochran

Reg. No. 46,632

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Lisa Posorske  
Name

Lisa Posorske  
Signature

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.

(GENERAL)



S/N 10/789,042

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Title: ATOMIC LAYER-DEPOSITED  $\text{LaAlO}_3$  FILMS FOR GATE DIELECTRICSSUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

MS Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Supplemental Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. §1.97(c)(2), Applicants hereby authorize the Commissioner to charge the fee of \$180.00 as set forth in 37 C.F.R. §1.17(p), to Deposit Account No. 19-0743. Please charge any additional fees or credit any overpayment to Deposit Account No. 19-0743.

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Pursuant to 37 C.F.R. 1.98(a)(2), Applicant believes that copies of cited U.S. Patents and Published Applications are no longer required to be provided to the Office. Notification of this change was provided in the United States Patent and Trademark Office OG Notices dated October 12, 2004. Thus, Applicant has not included copies of any US Patents or Published Applications cited with this submission. Should the Office require copies to be provided, Applicant respectfully requests that notice of such requirement be directed to Applicant's below-signed representative. Applicant acknowledges the requirement to submit copies of foreign patent documents and non-patent literature in accordance with 37 C.F.R. 1.98(a)(2).

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.


Respectfully submitted,

KIE Y. AHN ET AL.

By their Representatives,

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Date 25 May 2006

By   
David R. Cochran  
Reg. No. 46,632

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Application Number	10/789,042
Filing Date	February 27, 2004
First Named Inventor	Ahn, Kie
Group Art Unit	2815
Examiner Name	Wilson, Allan

Attorney Docket No: 1303.050US2

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**Filing Date** February 27, 2004  
**First Named Inventor** Ahn, Kie  
**Group Art Unit** 2815  
**Examiner Name** Wilson, Allan

Sheet 2 of 4

Attorney Docket No: 1303.050US2

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Examiner Name	Wilson, Allan

Sheet 3 of 4

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Sheet 4 of 4

Attorney Docket No: 1303.050US2

Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	?
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## OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issuе number(s), publisher, city and/or country where published.	?
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